SESSION 3
GaN MANUFACTURING

Chairs: Dane Henry, Qorvo, Inc.
Toshihide Kikkawa, Transphorm, Inc.

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The GaN Manufacturing session will feature a variety of topics ranging from process technology to visual yield improvement to high power plastic packaging for GaN. The session begins with a paper from Qorvo describing a 0.15µm GaN MMIC technology for 2-50GHz applications. The next paper is from WIN Semiconductors and discusses RF performance improvements on a 0.25µm GaN HEMT technology by optimizing the SiN passivation and using a source slot via design. The third paper is from Mitsubishi Electric and investigates the impact of underlying metals on the texture of plated Au films on GaN. This is followed by another paper from WIN Semiconductors describing changes in the substrate via etch stop metal and post-ICP etch clean for improved visual yields on substrate vias. The final paper of the session is from MACOM Technology Solutions and describes a new generation of high power plastic packaging for RF GaN devices.